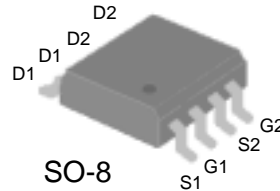


DUAL N-CANNEL ENHANCEMENT-MODE POWER MOSFET

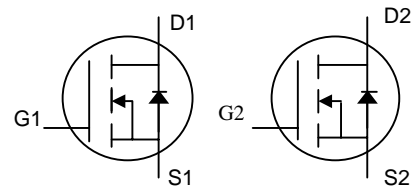
Low on-resistance
Simple drive requirement
Dual N-MOSFET package



BV_{DSS} 30V
 $R_{DS(ON)}$ 14m Ω
 I_D 10A

Description

Advanced power MOSFETs from Silicon Standard provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ\text{C}$	Continuous Drain Current ³	10	A
$I_D @ T_A=70^\circ\text{C}$	Continuous Drain Current ³	8	A
I_{DM}	Pulsed Drain Current ¹	30	A
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation	2	W
	Linear Derating Factor	0.016	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-a}	Thermal Resistance Junction-ambient ³	Max. 62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}, I_D=1\text{mA}$	-	0.03	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=10A$	-	-	14	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=7A$	-	-	20	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=10A$	-	16	-	S
I_{DSS}	Drain-Source Leakage Current ($T_j=25^\circ\text{C}$)	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
	Drain-Source Leakage Current ($T_j=70^\circ\text{C}$)	$V_{DS}=24V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_D=10A$	-	23	35	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=24V$	-	6	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	14	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=15V$	-	12	-	ns
t_r	Rise Time	$I_D=1A$	-	8	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	34	-	ns
t_f	Fall Time	$R_D=15\Omega$	-	16	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	1910	3070	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	400	-	pF
C_{riss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	280	-	pF
R_g	Gate Resistance	$f=1.0\text{MHz}$	-	0.9	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=1.7A, V_{GS}=0V$	-	-	1.2	V
t_{rr}	Reverse Recovery Time ²	$I_S=10A, V_{GS}=0V,$	-	30	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	24	-	nC

Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Surface mounted on 1 in² copper pad of FR4 board ; 135°C/W when mounted on min. copper pad.

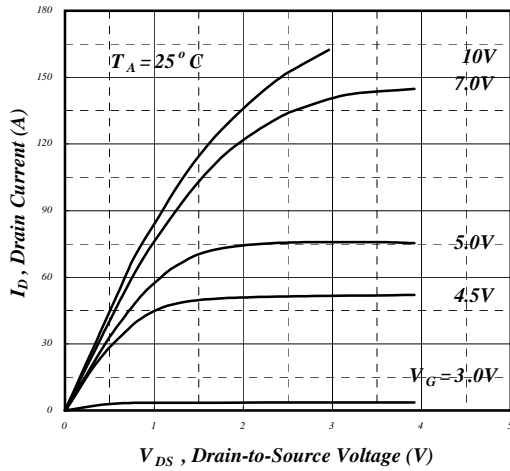


Fig 1. Typical Output Characteristics

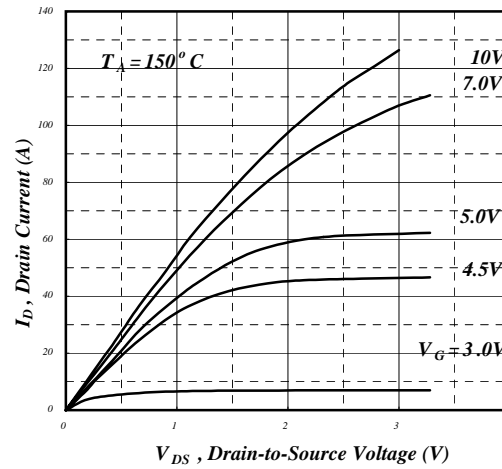


Fig 2. Typical Output Characteristics

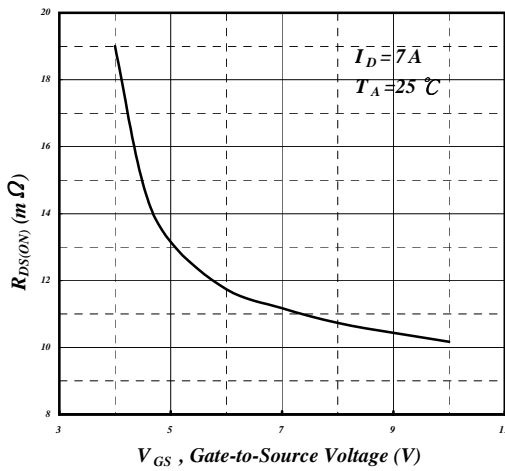


Fig 3. On-Resistance vs. Gate Voltage

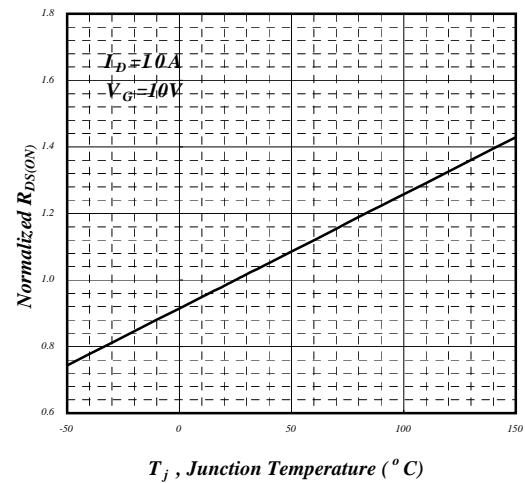


Fig 4. Normalized On-Resistance vs. Junction Temperature

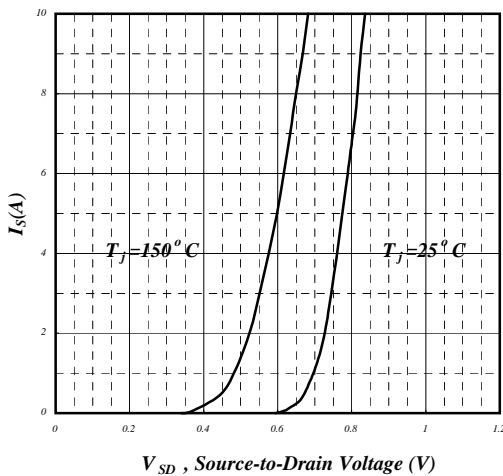


Fig 5. Forward Characteristic of Reverse Diode

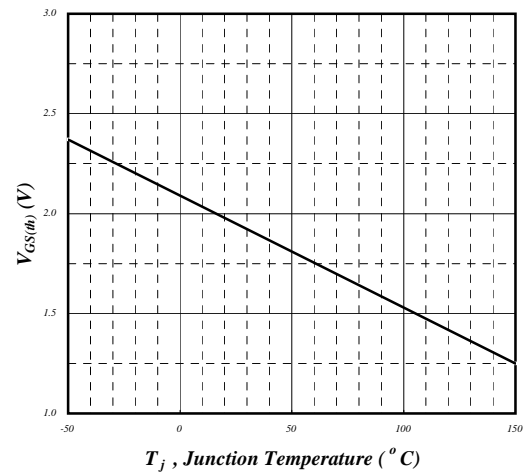


Fig 6. Gate Threshold Voltage vs. Junction Temperature

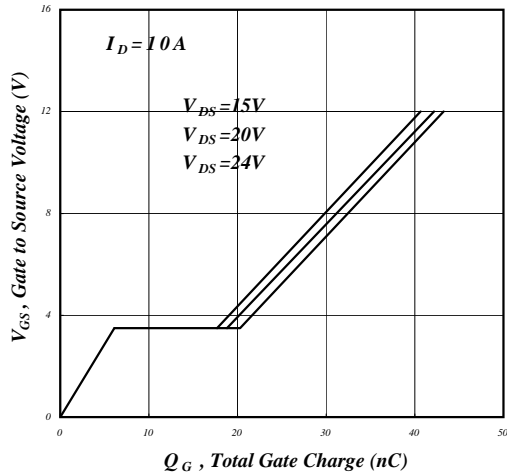


Fig 7. Gate Charge Characteristics

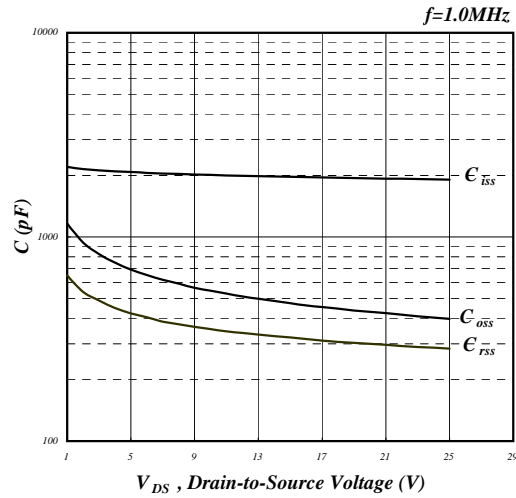


Fig 8. Typical Capacitance Characteristics

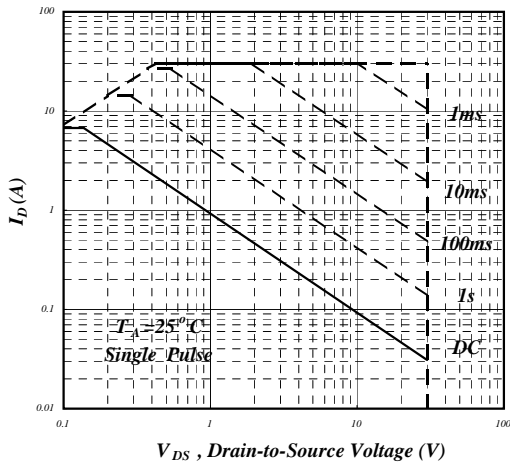


Fig 9. Maximum Safe Operating Area

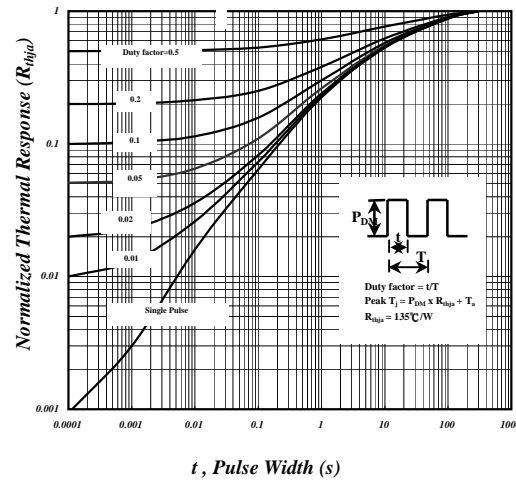


Fig 10. Effective Transient Thermal Impedance

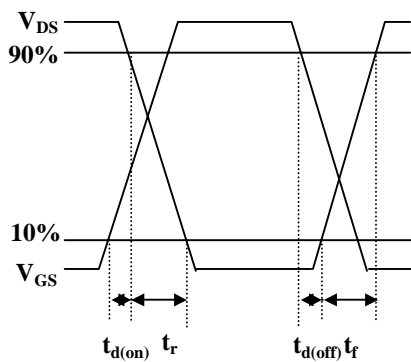


Fig 11. Switching Time Waveform

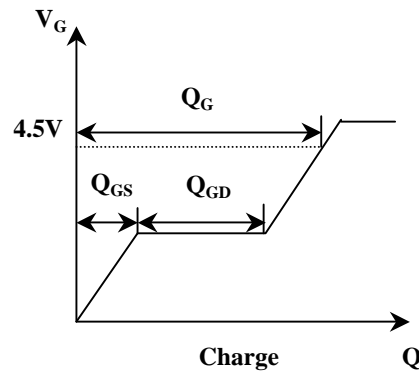


Fig 12. Gate Charge Waveform

Information furnished by Silicon Standard Corporation is believed to be accurate and reliable. However, Silicon Standard Corporation makes no guarantee or warranty, express or implied, as to the reliability, accuracy, timeliness or completeness of such information and assumes no responsibility for its use, or for infringement of any patent or other intellectual property rights of third parties that may result from its use. Silicon Standard reserves the right to make changes as it deems necessary to any products described herein for any reason, including without limitation enhancement in reliability, functionality or design. No license is granted, whether expressly or by implication, in relation to the use of any products described herein or to the use of any information provided herein, under any patent or other intellectual property rights of Silicon Standard Corporation or any third parties.